

Memory Module Specifications

KSM26RS8/8MEI

8GB 1Rx8 1G x 72-Bit PC4-2666

CL19 Registered w/Parity 288-Pin DIMM

DESCRIPTION

Kingston's KSM26RS8/8MEI is a 1G x 72-bit (8GB) DDR4-2666 CL19 SDRAM (Synchronous DRAM) registered w/ parity, 1Rx8, ECC, memory module, based on nine 1G x 8-bit FBGA components. The SPD is programmed to JEDEC standard latency DDR4-2666 timing of 19-19-19 at 1.2V. Each 288-pin DIMM uses gold contact fingers. The electrical and mechanical specifications are as follows:

FEATURES

- Power Supply: VDD = 1.2V
- VDDQ = 1.2V
- VPP = 2.5V
- VDDSPD = 2.25V to 2.75V
- Functionality and operations comply with the DDR4 SDRAM datasheet
- 16 internal banks
- Bank Grouping is applied, and CAS to CAS latency (tCCD_L, tCCD_S) for the banks in the same or different bank group accesses are available
- Data transfer rates: PC4-2666, PC4-2400, PC4-2133, PC4-1866, PC4-1600
- Bi-Directional Differential Data Strobe
- 8 bit pre-fetch
- Burst Length (BL) switch on-the-fly BL8 or BC4(Burst Chop)
- Supports ECC error correction and detection
- On-Die Termination (ODT)
- Temperature sensor with integrated SPD
- This product is in compliance with the RoHS directive.
- Per DRAM Addressability is supported
- Internal Vref DQ level generation is available
- Write CRC is supported at all speed grades
- CA parity (Command/Address Parity) mode is supported

SPECIFICATIONS

CL(IDD)	19 cycles
Row Cycle Time (tRCmin)	45.75ns(min.)
Refresh to Active/Refresh Command Time (tRFCmin)	350ns(min.)
Row Active Time (tRASmin)	32ns(min.)
Maximum Operating Power	AUR*
UL Rating	94 V - 0
Operating Temperature	0° C to +85° C
Storage Temperature	-55° C to +100° C

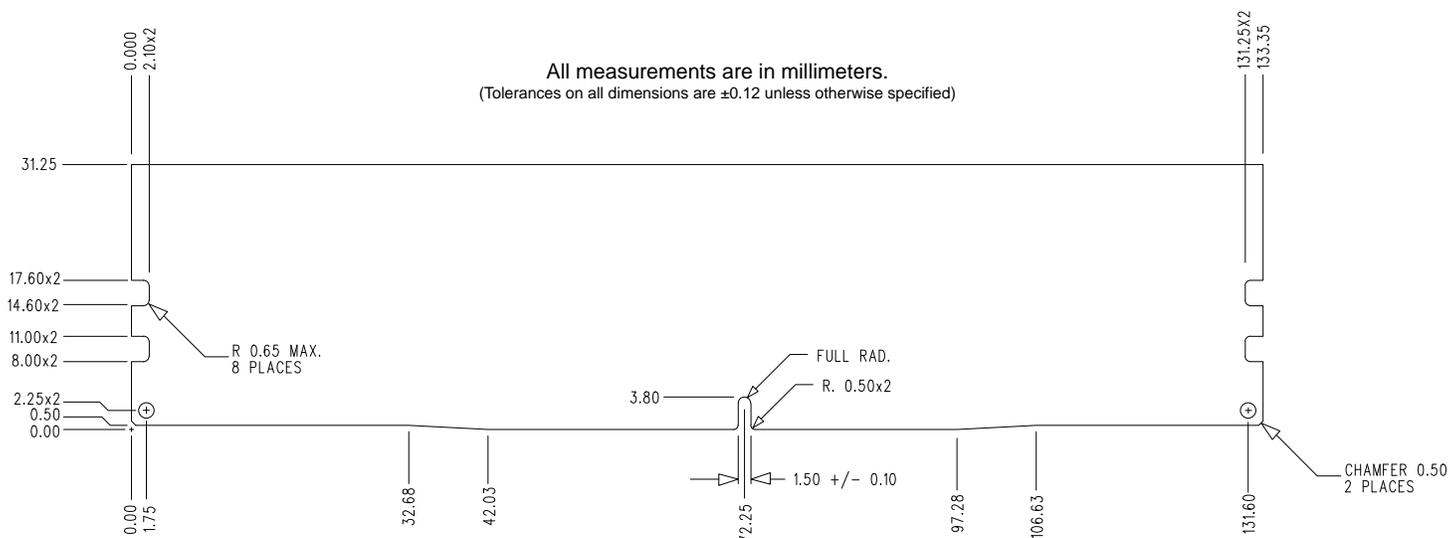
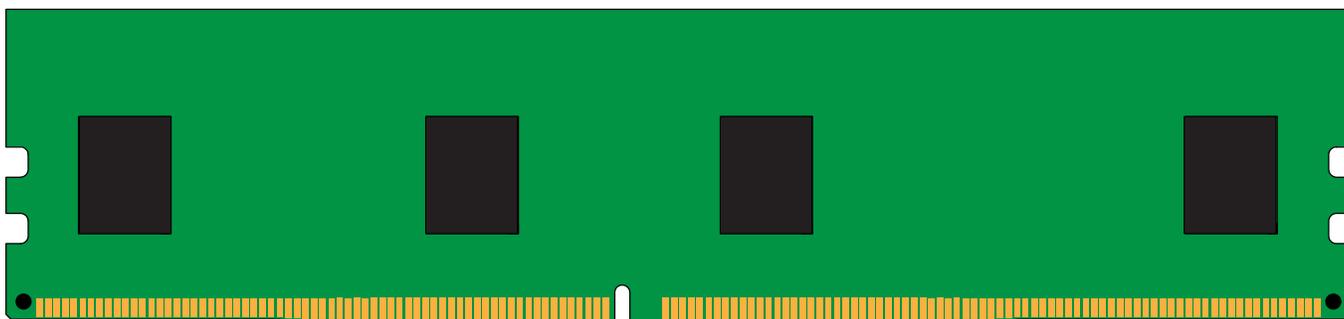
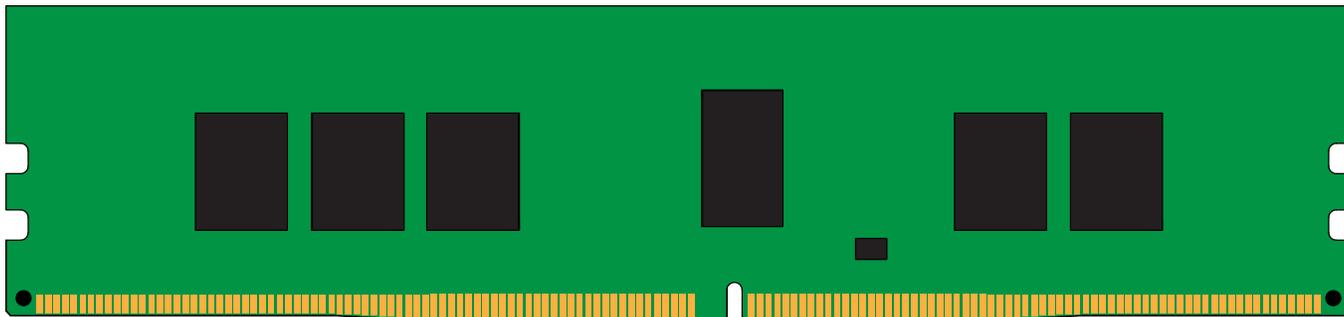
* Available Upon Request

Module Assembly

DRAM: MICRON (E-DIE)
RCD: IDT

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MODULE DIMENSIONS



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